

NSS20600CF8T1G

20 V, 7.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

- This is a Pb-Free Device

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

| Rating | Symbol | Max | Unit |
|--------------------------------|-----------|----------------------------|------|
| Collector-Emitter Voltage | V_{CEO} | -20 | Vdc |
| Collector-Base Voltage | V_{CBO} | -20 | Vdc |
| Emitter-Base Voltage | V_{EBO} | -7.0 | Vdc |
| Collector Current - Continuous | I_C | -6.0 | Adc |
| Collector Current - Peak | I_{CM} | -7.0 | A |
| Electrostatic Discharge | ESD | HBM Class 3B MM Class C | |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|---------------------------------------|----------------|----------------------------|
| Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D (Note 1) | 830 6.7 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ (Note 1) | 150 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D (Note 2) | 1.4 11.1 | W mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ (Note 2) | 90 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-Lead #1 | $R_{\theta JL}$ (Note 2) | 15 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation (Single Pulse < 10 sec) | $P_{D\text{single}}$ (Notes 2 & 3) | 2.75 | W |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

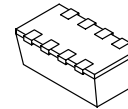
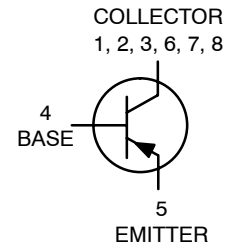
1. FR-4 @ 100 mm², 1 oz copper traces.
2. FR-4 @ 500 mm², 1 oz copper traces.
3. Thermal response.



ON Semiconductor[®]

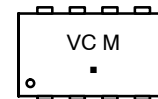
<http://onsemi.com>

-20 VOLTS, 7.0 AMPS PNP LOW $V_{CE(sat)}$ TRANSISTOR EQUIVALENT $R_{DS(on)}$ 50 m Ω



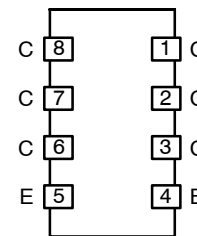
ChipFET[™]
CASE 1206A
STYLE 4

MARKING DIAGRAM



VC = Specific Device Code
M = Date Code
▪ = Pb-Free Package

PIN CONNECTIONS



ORDERING INFORMATION

| Device | Package | Shipping [†] |
|----------------|----------------------|-----------------------|
| NSS20600CF8T1G | ChipFET (Pb-Free) | 3000/ Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSS20600CF8T1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typical | Max | Unit |
|--|----------------------|------|---------|------|------------------|
| OFF CHARACTERISTICS | | | | | |
| Collector - Emitter Breakdown Voltage (I _C = -10 mA, I _B = 0) | V _{(BR)CEO} | -20 | - | - | Vdc |
| Collector - Base Breakdown Voltage (I _C = -0.1 mA, I _E = 0) | V _{(BR)CBO} | -20 | - | - | Vdc |
| Emitter - Base Breakdown Voltage (I _E = -0.1 mA, I _C = 0) | V _{(BR)EBO} | -7.0 | - | - | Vdc |
| Collector Cutoff Current (V _{CB} = -20 Vdc, I _E = 0) | I _{CBO} | - | - | -0.1 | μA _{dc} |
| Emitter Cutoff Current (V _{EB} = -7.0 Vdc) | I _{EBO} | - | - | -0.1 | μA _{dc} |

ON CHARACTERISTICS

| | | | | | |
|--|----------------------|---------------------------------|--|--|-----|
| DC Current Gain (Note 4) (I _C = -10 mA, V _{CE} = -2.0 V) (I _C = -500 mA, V _{CE} = -2.0 V) (I _C = -1.0 A, V _{CE} = -2.0 V) (I _C = -2.0 A, V _{CE} = -2.0 V) (I _C = -3.0 A, V _{CE} = -2.0 V) | h _{FE} | 250 250 220 200 180 | - - 300 - - | - - - - - | |
| Collector - Emitter Saturation Voltage (Note 4) (I _C = -0.1 A, I _B = -0.010 A) (Note 5) (I _C = -1.0 A, I _B = -0.100 A) (I _C = -1.0 A, I _B = -0.010 A) (I _C = -2.0 A, I _B = -0.020 A) (I _C = -3.0 A, I _B = -0.030 A) (I _C = -4.0 A, I _B = -0.400 A) | V _{CE(sat)} | - - - - - - | -0.007 -0.050 -0.065 -0.090 -0.140 -0.160 | -0.010 -0.060 -0.080 -0.130 -0.180 -0.200 | V |
| Base - Emitter Saturation Voltage (Note 4) (I _C = -1.0 A, I _B = -0.01 A) | V _{BE(sat)} | - | - | -0.90 | V |
| Base - Emitter Turn-on Voltage (Note 4) (I _C = -2.0 A, V _{CE} = -3.0 V) | V _{BE(on)} | - | - | -0.90 | V |
| Cutoff Frequency (I _C = -100 mA, V _{CE} = -5.0 V, f = 100 MHz) | f _T | 100 | - | - | MHz |
| Input Capacitance (V _{EB} = -0.5 V, f = 1.0 MHz) | C _{ibo} | - | - | 700 | pF |
| Output Capacitance (V _{CB} = -3.0 V, f = 1.0 MHz) | C _{obo} | - | - | 280 | pF |

SWITCHING CHARACTERISTICS

| | | | | | |
|---|----------------|---|---|-----|----|
| Delay (V _{CC} = -15 V, I _C = 750 mA, I _{B1} = 15 mA) | t _d | - | - | 120 | ns |
| Rise (V _{CC} = -15 V, I _C = 750 mA, I _{B1} = 15 mA) | t _r | - | - | 250 | ns |
| Storage (V _{CC} = -15 V, I _C = 750 mA, I _{B1} = 15 mA) | t _s | - | - | 400 | ns |
| Fall (V _{CC} = -15 V, I _C = 750 mA, I _{B1} = 15 mA) | t _f | - | - | 250 | ns |

- Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%.
- Guaranteed by design but not tested.

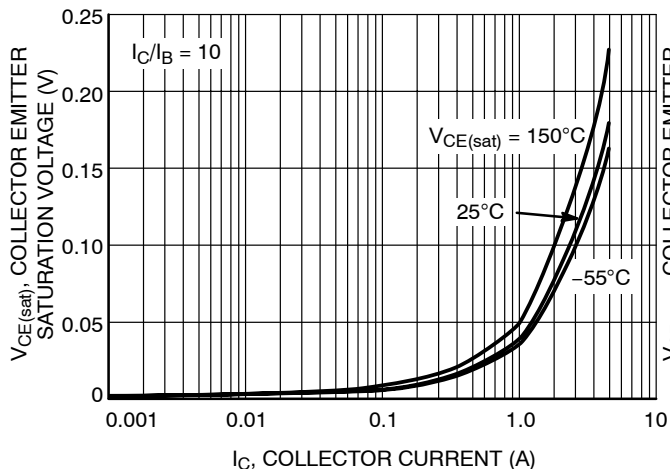


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

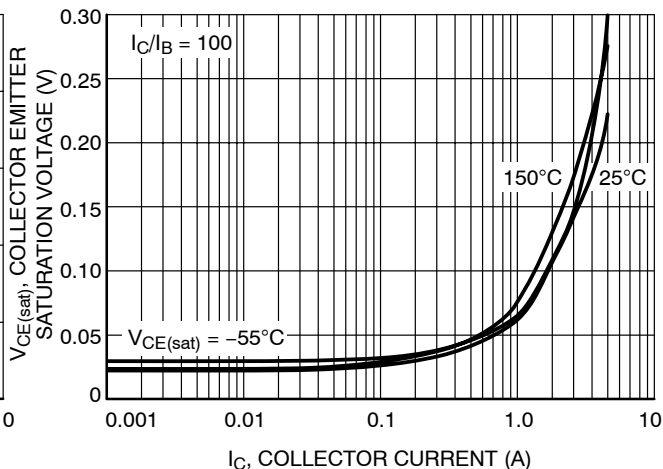


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

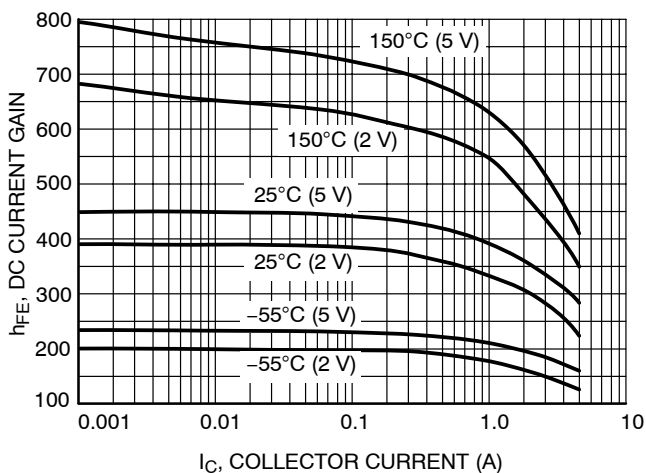


Figure 3. DC Current Gain vs. Collector Current

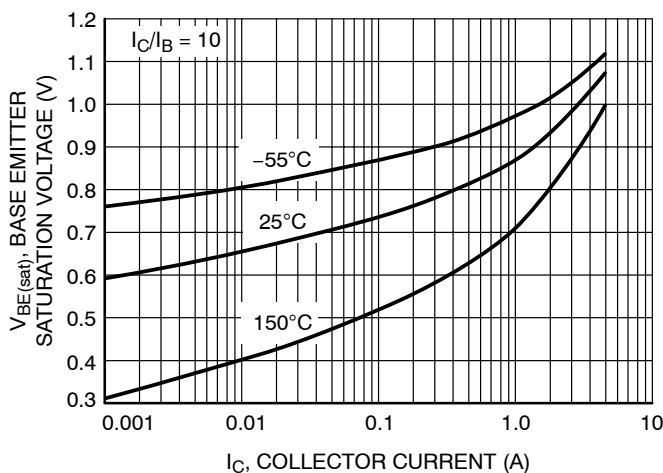


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

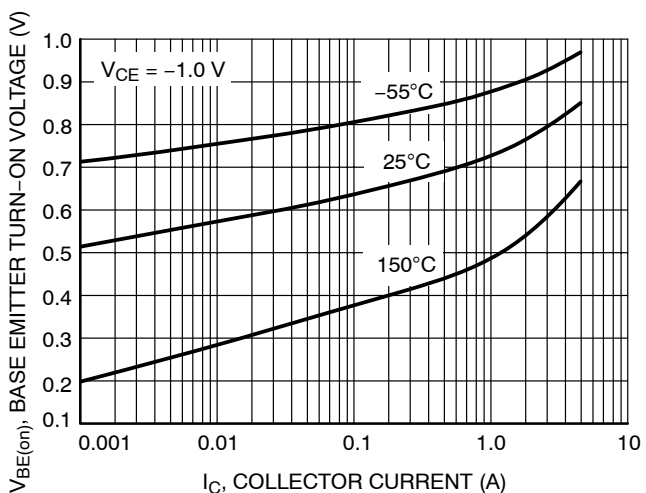


Figure 5. Base Emitter Turn-On Voltage vs. Collector Current

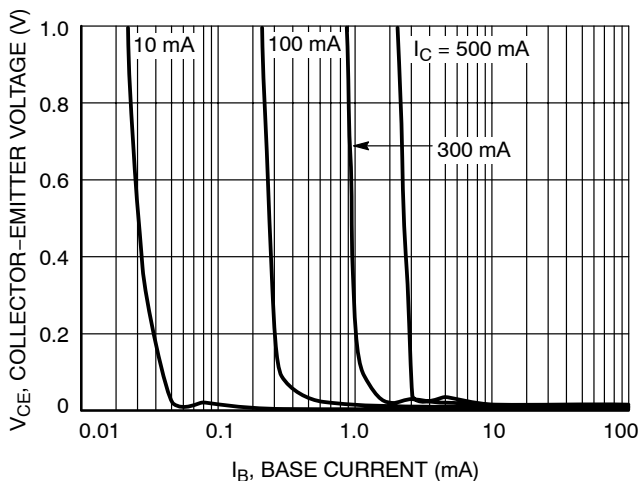


Figure 6. Saturation Region

NSS20600CF8T1G

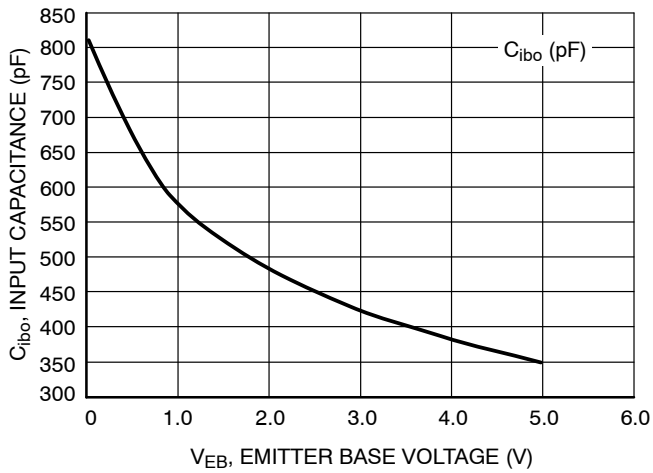


Figure 7. Input Capacitance

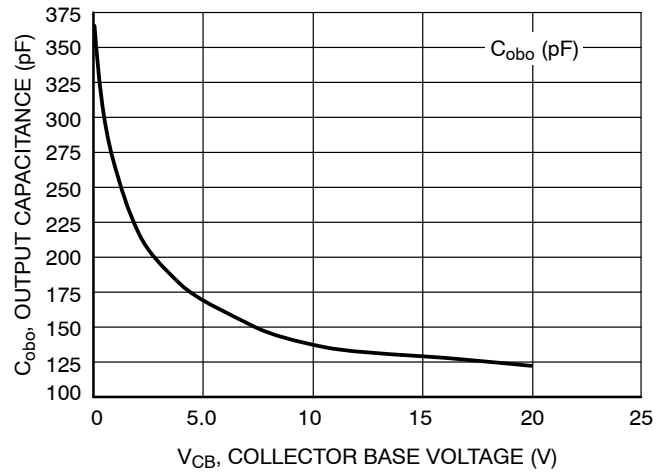


Figure 8. Output Capacitance

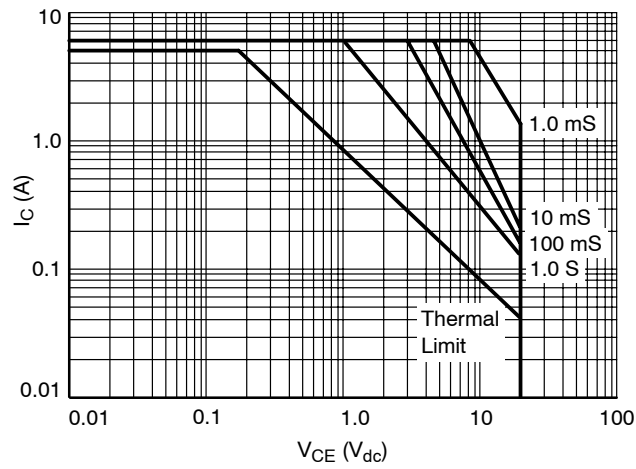


Figure 9. Safe Operating Area

MECHANICAL CASE OUTLINE

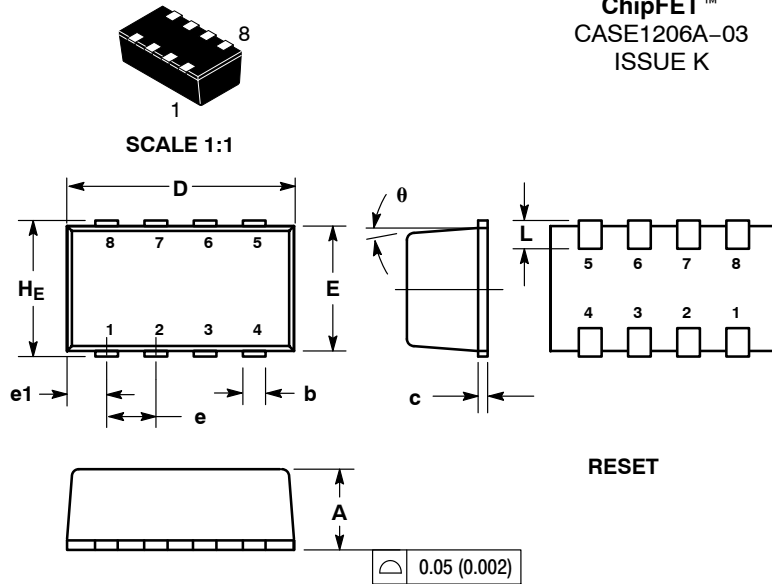
PACKAGE DIMENSIONS

ON Semiconductor®



ChipFET™ CASE1206A-03 ISSUE K

DATE 19 MAY 2009



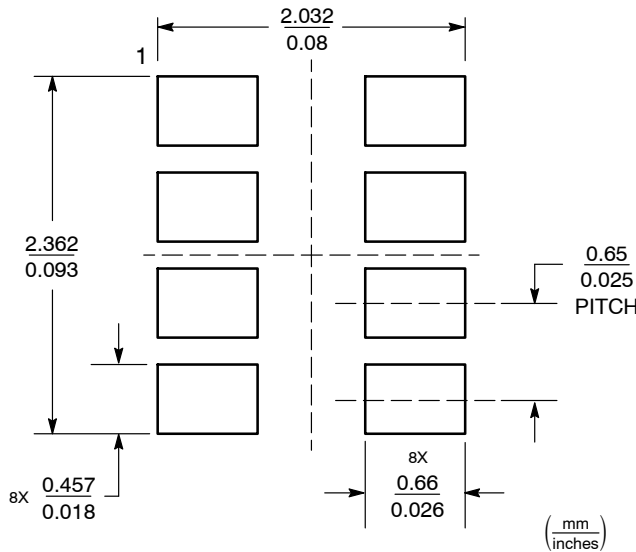
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 1.00 | 1.05 | 1.10 | 0.039 | 0.041 | 0.043 |
| b | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |
| c | 0.10 | 0.15 | 0.20 | 0.004 | 0.006 | 0.008 |
| D | 2.95 | 3.05 | 3.10 | 0.116 | 0.120 | 0.122 |
| E | 1.55 | 1.65 | 1.70 | 0.061 | 0.065 | 0.067 |
| e | 0.65 BSC | | | 0.025 BSC | | |
| e1 | 0.55 BSC | | | 0.022 BSC | | |
| L | 0.28 | 0.35 | 0.42 | 0.011 | 0.014 | 0.017 |
| HE | 1.80 | 1.90 | 2.00 | 0.071 | 0.075 | 0.079 |
| θ | 5° NOM | | | 5° NOM | | |

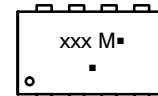
- | | | | | | |
|---|---|---|--|---|---|
| STYLE 1: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. GATE 5. SOURCE 6. DRAIN 7. DRAIN 8. DRAIN | STYLE 2: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1 | STYLE 3: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE | STYLE 4: PIN 1. COLLECTOR 2. COLLECTOR 3. COLLECTOR 4. BASE 5. EMITTER 6. COLLECTOR 7. COLLECTOR 8. COLLECTOR | STYLE 5: PIN 1. ANODE 2. ANODE 3. DRAIN 4. DRAIN 5. SOURCE 6. GATE 7. CATHODE 8. CATHODE | STYLE 6: PIN 1. ANODE 2. DRAIN 3. DRAIN 4. GATE 5. SOURCE 6. DRAIN 7. DRAIN 8. CATHODE / DRAIN |
|---|---|---|--|---|---|

SOLDERING FOOTPRINT



Basic Style

GENERIC MARKING DIAGRAM*



- xxx = Specific Device Code
 - M = Month Code
 - = Pb-Free Package
- (Note: Microdot may be in either location)

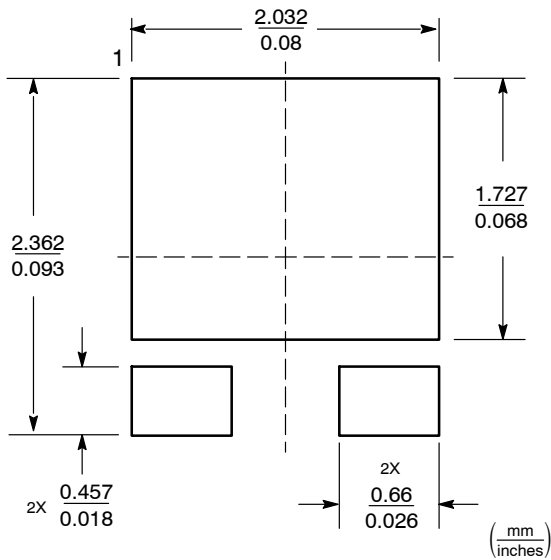
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

OPTIONAL SOLDERING FOOTPRINTS ON PAGE 2

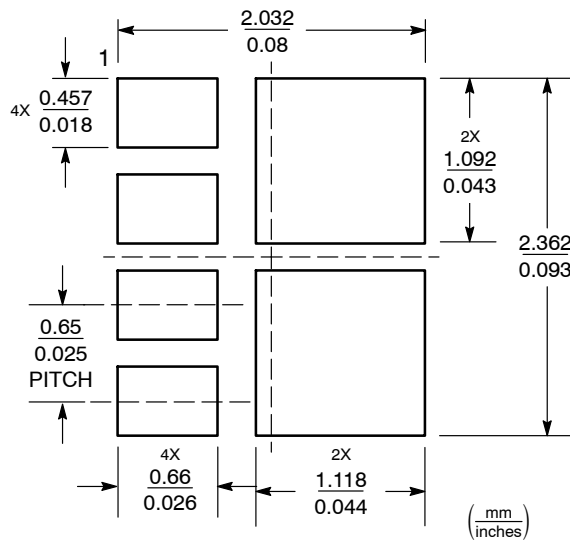
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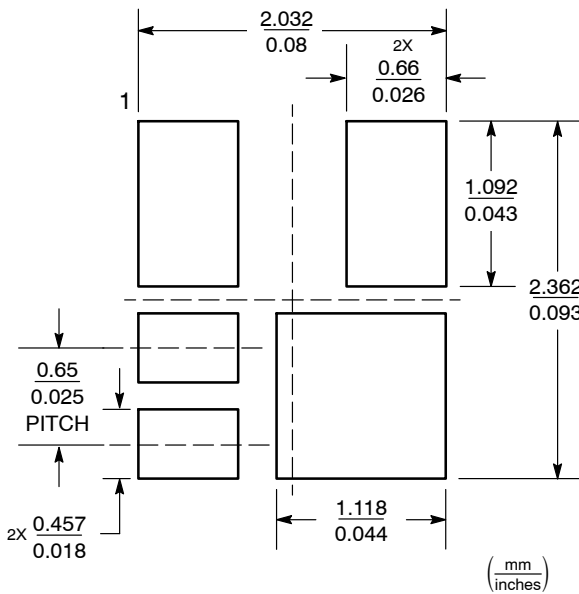
ADDITIONAL SOLDERING FOOTPRINTS*



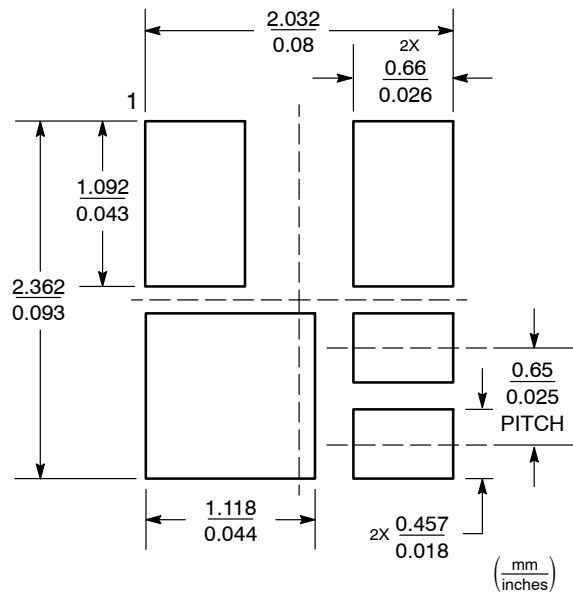
Styles 1 and 4



Style 2



Style 3



Style 5

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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